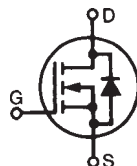


High Voltage Power MOSFET

IXTT6N150 IXTH6N150

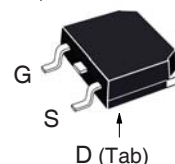
$V_{DSS} = 1500V$
 $I_{D25} = 6A$
 $R_{DS(on)} \leq 3.5\Omega$

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode

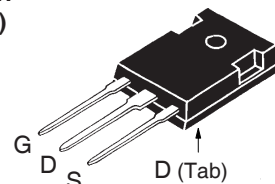


| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 1500 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 1500 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | 6 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 24 | A |
| I_A | $T_C = 25^\circ C$ | 3 | A |
| E_{AS} | $T_C = 25^\circ C$ | 500 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 5 | V/ns |
| P_D | $T_C = 25^\circ C$ | 540 | W |
| T_J | | - 55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | - 55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque (TO-247) | 1.13 / 10 | Nm/lb.in. |
| Weight | TO-268 | 4 | g |
| | TO-247 | 6 | g |

TO-268
(IXTT)



TO-247
(IXTH)



G = Gate D = Drain
 S = Source Tab = Drain

Features

- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification
- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 1500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 25 μA 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 3.5 Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 4.0 | 6.5 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 2230 | pF |
| C_{oss} | | | 170 | pF |
| C_{rss} | | | 64 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External) | | 22 | ns |
| t_r | | | 20 | ns |
| $t_{d(off)}$ | | | 50 | ns |
| t_f | | | 38 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 67 | nC |
| Q_{gs} | | | 12 | nC |
| Q_{gd} | | | 36 | nC |
| R_{thJC} | | | | 0.23 $^\circ\text{C/W}$ |
| R_{thCS} | TO-247 | | 0.21 | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 6 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 24 A |
| V_{SD} | $I_F = 6\text{A}$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.3 V |
| t_{rr} | $I_F = 3\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$ | | 1.5 | μs |
| I_{RM} | | | 12 | A |
| Q_{RM} | | | 9 | μC |

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

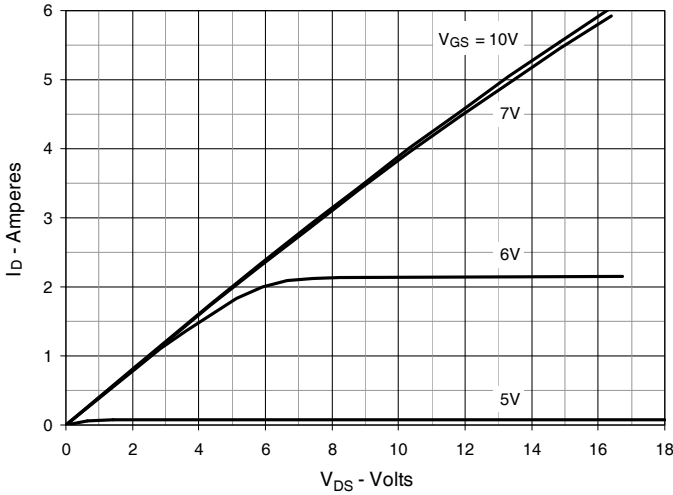


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

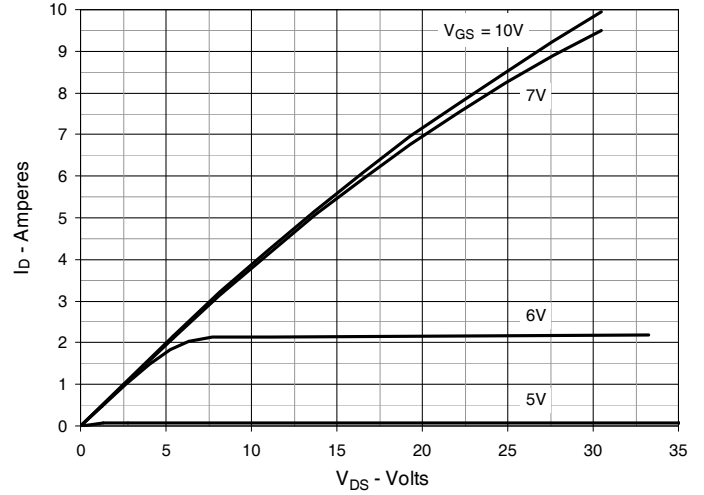


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

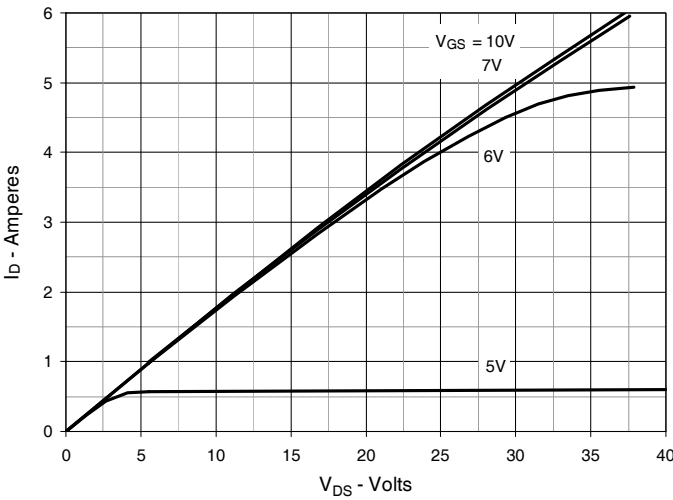


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 3\text{A}$ Value vs. Junction Temperature

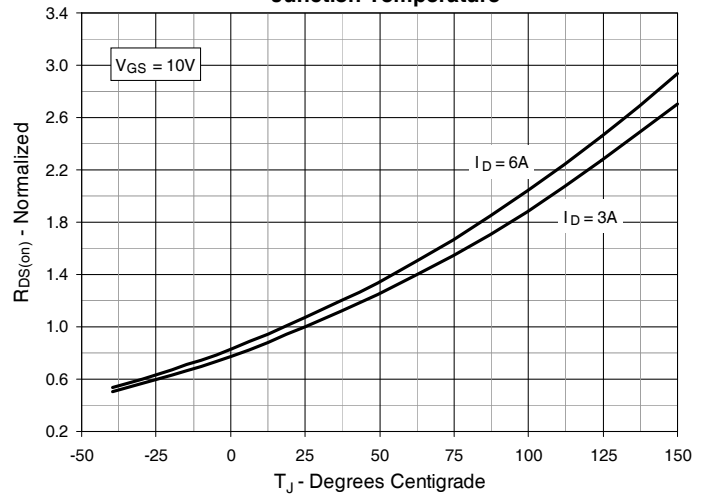


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 3\text{A}$ Value vs. Drain Current

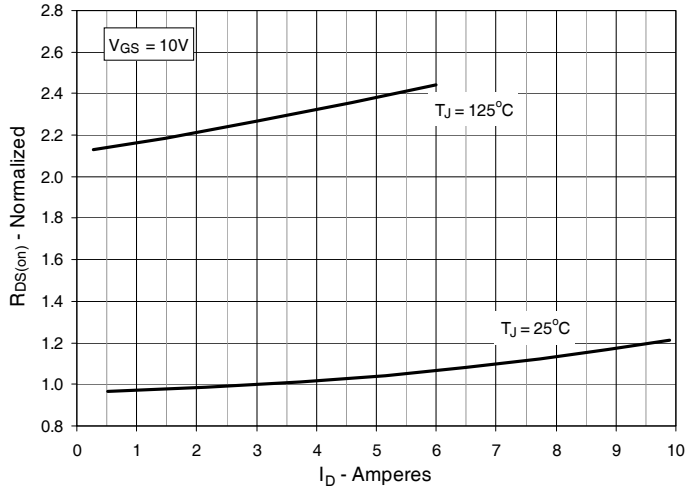


Fig. 6. Maximum Drain Current vs. Case Temperature

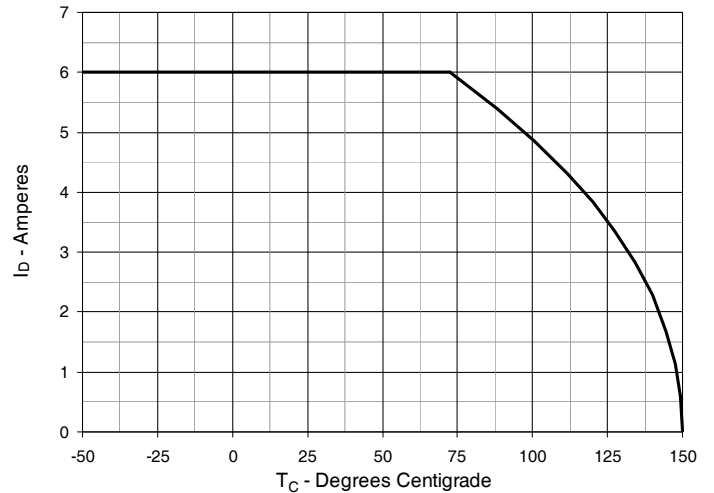


Fig. 7. Input Admittance

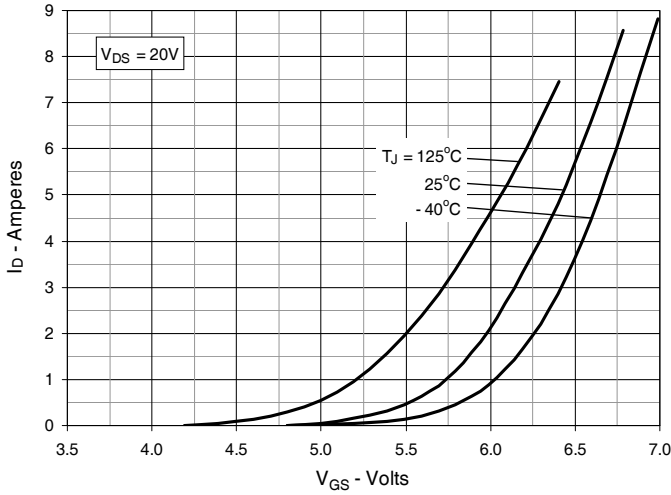


Fig. 8. Transconductance

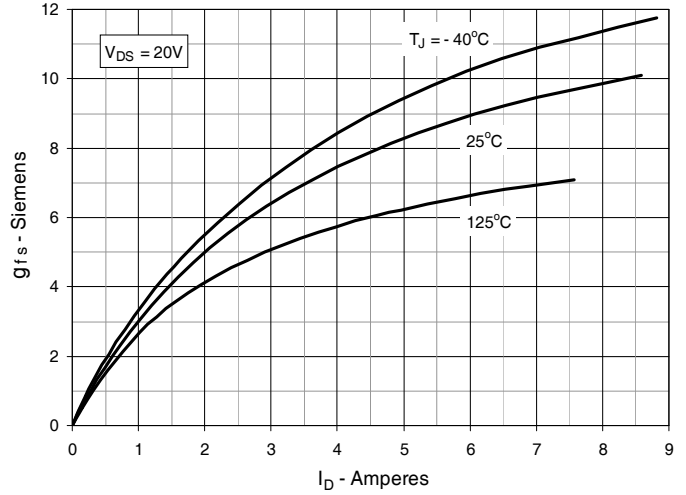


Fig. 9. Forward Voltage Drop of Intrinsic Diode

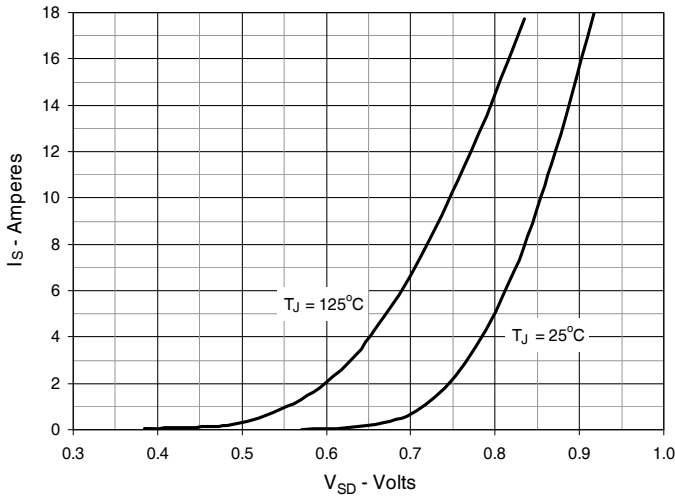


Fig. 10. Gate Charge

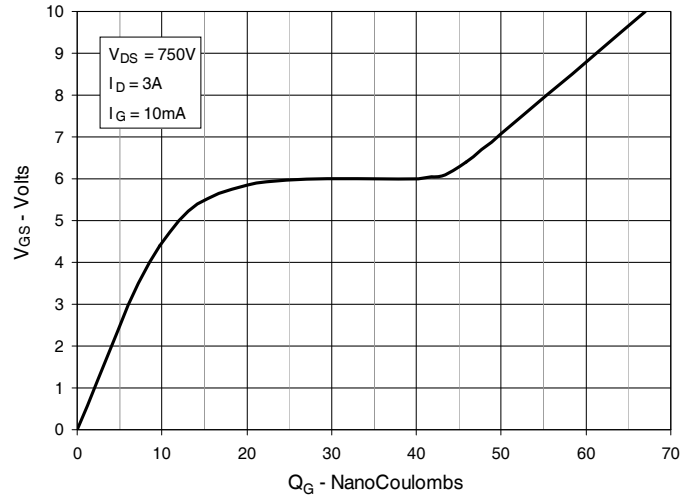


Fig. 11. Capacitance

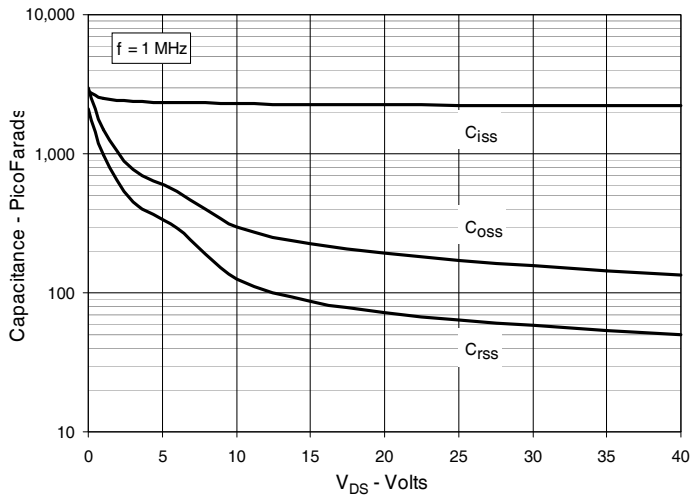


Fig. 12. Forward-Bias Safe Operating Area

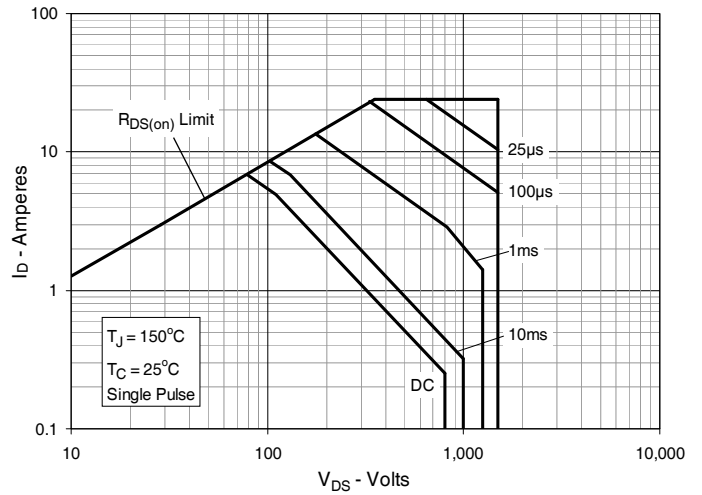
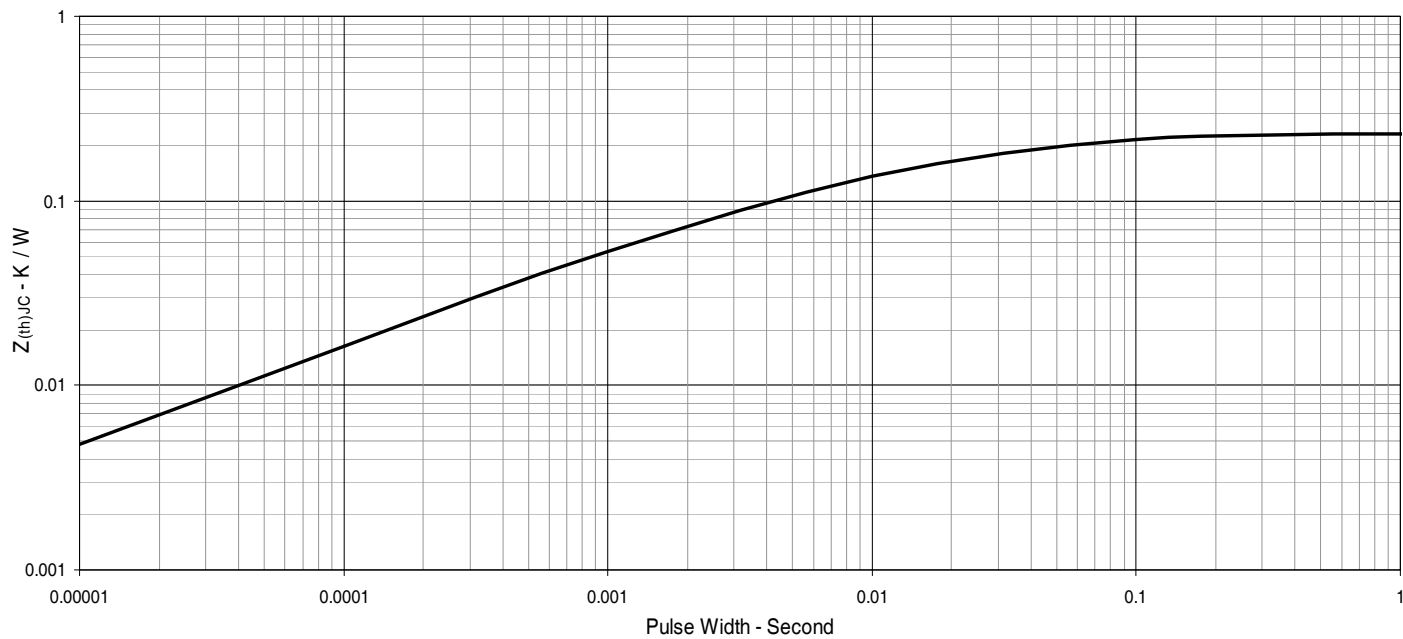
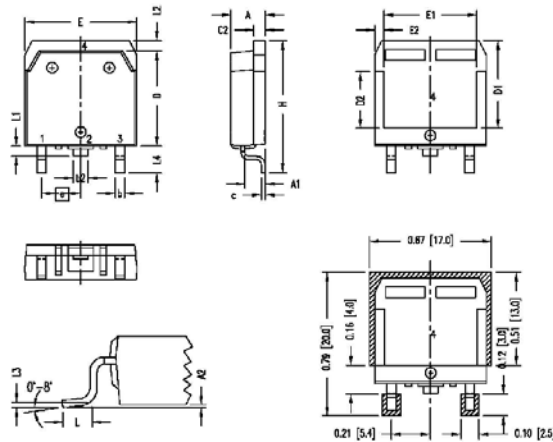


Fig. 13. Maximum Transient Thermal Impedance



TO-268 Outline



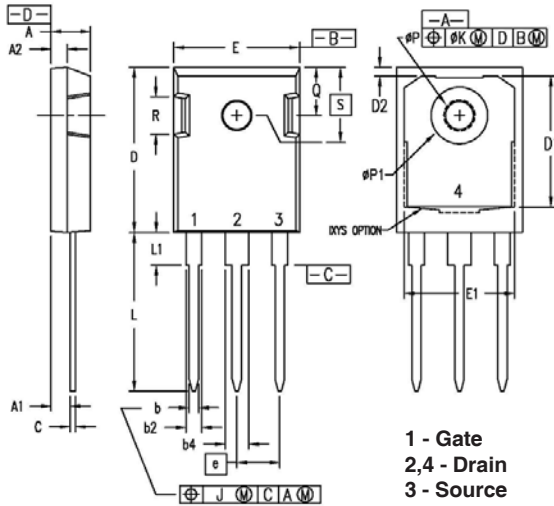
- 1 - Gate
- 2,4 - Drain
- 3 - Source

RECOMMENDED MINIMUM FOOT PRINT FOR SMD

| SYMBOL | INCHES | | MILLIMETERS | |
|--------|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .193 | .201 | 4.90 | 5.10 |
| A1 | .106 | .114 | 2.70 | 2.90 |
| A2 | .001 | .010 | 0.02 | 0.25 |
| b | .045 | .057 | 1.15 | 1.45 |
| b2 | .075 | .083 | 1.90 | 2.10 |
| C | .016 | .026 | 0.40 | 0.65 |
| C2 | .057 | .063 | 1.45 | 1.60 |
| D | .543 | .551 | 13.80 | 14.00 |
| D1 | .488 | .500 | 12.40 | 12.70 |
| D2 | .320 | .335 | 8.13 | 8.50 |
| E | .624 | .632 | 15.85 | 16.05 |
| E1 | .524 | .535 | 13.30 | 13.60 |
| E2 | .045 | .055 | 1.14 | 1.39 |
| e | .215 BSC | | 5.45 BSC | |
| H | .736 | .752 | 18.70 | 19.10 |
| L | .094 | .106 | 2.40 | 2.70 |
| L1 | .047 | .055 | 1.20 | 1.40 |
| L2 | .039 | .045 | 1.00 | 1.15 |
| L3 | .010 BSC | | 0.25 BSC | |
| L4 | .150 | .161 | 3.80 | 4.10 |

NOTE: ALL METAL SURFACE ARE WHITE PURE TIN PLATED EXCEPT TRIM AREA.
Pd PLATING THICKNESS (4 - 20 um)

TO-247 Outline



- 1 - Gate
- 2,4 - Drain
- 3 - Source

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|----------|-------------|----------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .090 | .100 | 2.29 | 2.54 |
| A2 | .075 | .085 | 1.91 | 2.16 |
| b | .045 | .055 | 1.14 | 1.40 |
| b2 | .075 | .087 | 1.91 | 2.20 |
| b4 | .115 | .126 | 2.92 | 3.20 |
| C | .024 | .031 | 0.61 | 0.80 |
| D | .819 | .840 | 20.80 | 21.34 |
| D1 | .650 | .690 | 16.51 | 17.53 |
| D2 | .035 | .050 | 0.89 | 1.27 |
| E | .620 | .635 | 15.75 | 16.13 |
| E1 | .545 | .565 | 13.84 | 14.35 |
| e | .215 BSC | | 5.45 BSC | |
| J | -- | .010 | -- | 0.25 |
| K | -- | .025 | -- | 0.64 |
| L | .780 | .810 | 19.81 | 20.57 |
| L1 | .150 | .170 | 3.81 | 4.32 |
| øP1 | .140 | .144 | 3.55 | 3.65 |
| øP1 | .275 | .290 | 6.99 | 7.37 |
| Q | .220 | .244 | 5.59 | 6.20 |
| R | .170 | .190 | 4.32 | 4.83 |
| S | | .242 BSC | | 6.15 BSC |

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)



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